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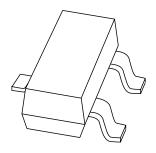
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PMMT491A NPN BISS transistor

Product data sheet Supersedes data of 2001 Jun 11 2004 Jan 13



NPN BISS transistor

PMMT491A

FEATURES

- High current (max. 1 A)
- Low collector-emitter saturation voltage ensures reduced power consumption.

APPLICATIONS

 Battery powered units where high current and low power consumption are important.

DESCRIPTION

NPN BISS (Breakthrough In Small Signal) transistor in a SOT23 plastic package. PNP complement: PMMT591A.

MARKING

| TYPE NUMBER | MARKING CODE ⁽¹⁾ |
|-------------|-----------------------------|
| PMMT491A | 9A* |

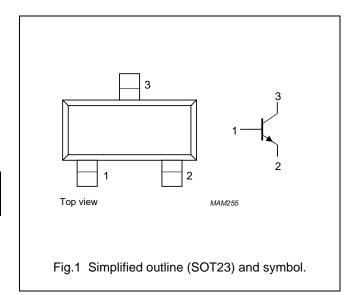
Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.

* = W : Made in China.

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | base |
| 2 | emitter |
| 3 | collector |



ORDERING INFORMATION

| TYPE | PACKAGE | | |
|----------|---------|--|---------|
| NUMBER | NAME | DESCRIPTION | VERSION |
| PMMT491A | _ | plastic surface mounted package; 3 leads | SOT23 |

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | _ | 40 | V |
| V _{CEO} | collector-emitter voltage | open base | _ | 40 | V |
| V_{EBO} | emitter-base voltage | open collector | _ | 5 | V |
| I _C | collector current (DC) | | _ | 1 | Α |
| I _{CM} | peak collector current | | _ | 2 | Α |
| I _{BM} | peak base current | | _ | 1 | Α |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C; note 1 | _ | 250 | mW |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 150 | °C |
| T _{amb} | operating ambient temperature | | -65 | +150 | °C |

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN BISS transistor

PMMT491A

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|----------------------|---|------------|-------|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | note 1 | 500 | K/W |

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------------------|--------------------------------------|---|------|------|------|
| I _{CBO} | collector cut-off current | I _E = 0; V _{CB} = 30 V | _ | 100 | nA |
| I _{CEO} | collector cut-off current | I _B = 0; V _{CE} = 30 V | _ | 100 | nA |
| I _{EBO} | emitter cut-off current | I _C = 0; V _{EB} = 5 V | _ | 100 | nA |
| h _{FE} | DC current gain | V _{CE} = 5 V; note 1 | | | |
| | | I _C = 1 mA | 300 | _ | |
| | | I _C = 500 mA | 300 | 900 | |
| | | I _C = 1 A | 200 | _ | |
| V _{CEsat} | collector-emitter saturation voltage | note 1 | | | |
| | | $I_C = 100 \text{ mA}; I_B = 1 \text{ mA}$ | _ | 200 | mV |
| | | $I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$ | _ | 300 | mV |
| | | I _C = 1 A; I _B = 100 mA | _ | 500 | mV |
| V _{BEsat} | base-emitter saturation voltage | I _C = 1 A; I _B = 100 mA; note 1 | _ | 1.2 | V |
| V _{BE} | base-emitter voltage | V _{CE} = 5 V; I _C = 1 A; note 1 | _ | 1.1 | V |
| C _c | collector capacitance | I _E = I _e = 0; V _{CB} = 10 V; f = 1 MHz | _ | 10 | pF |
| f _T | transition frequency | $I_C = 50 \text{ mA}$; $V_{CE} = 10 \text{ V}$; $f = 100 \text{ MHz}$ | 150 | _ | MHz |

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

NPN BISS transistor

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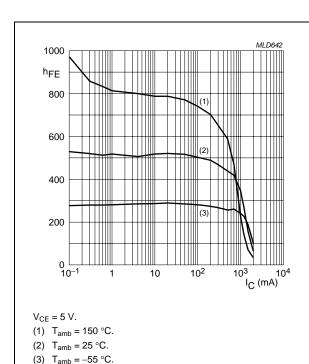
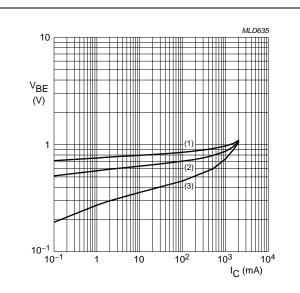


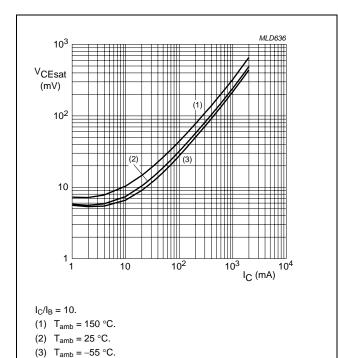
Fig.2 DC current gain as a function of collector current; typical values.

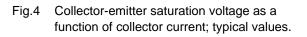


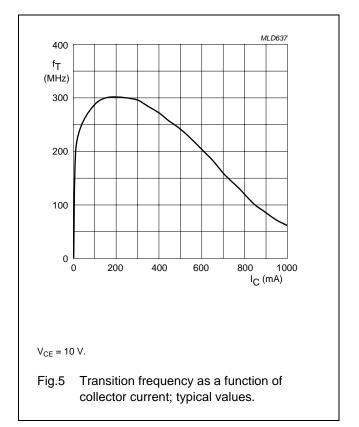
V_{CE} = 5 V.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.3 Base-emitter voltage as a function of collector current; typical values.







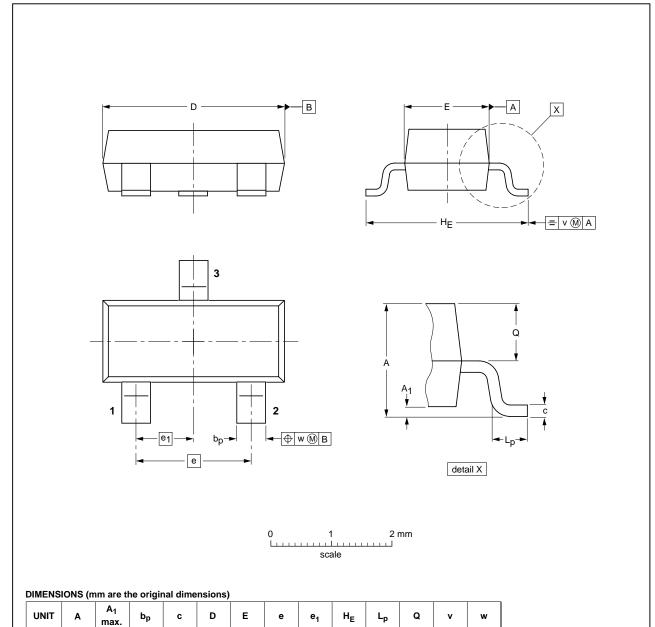
NPN BISS transistor

PMMT491A

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



| OUTLINE | REFERENCES | | EUROPEAN | ICCUE DATE | | |
|---------|------------|----------|----------|------------|------------|-----------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT23 | | TO-236AB | | | | -04-11-04- 06-03-16 |

0.95

1.9

0.45

0.55

0.2

0.1

2004 Jan 13 5

max.

0.9

0.48

0.38

0.15

0.09

NPN BISS transistor

PMMT491A

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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